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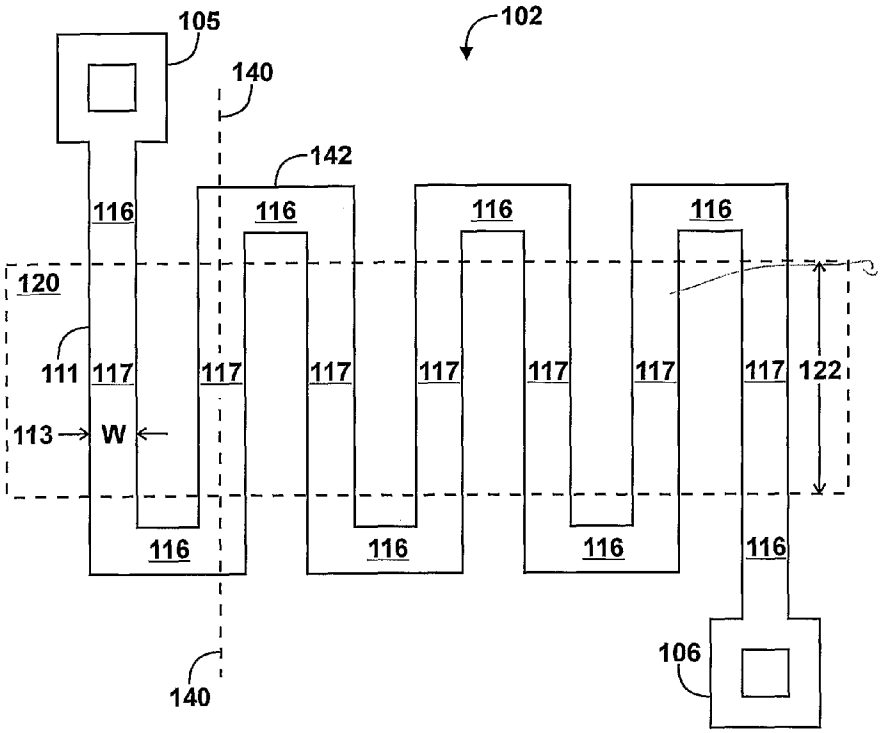
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(54) Title: METHOD OF FORMING RESISTIVE STRUCTURES



(57) Abstract: A resistive structure (102) formed overlying a semiconductor substrate is masked with a silicide block layer (120) to define a portion of the resistive structure that is to be unsilicided and a portion of the resistive structure to be silicided. The silicide block layer (120) is changed to facilitate different processes.

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